

DATA SHEET



BCX19

NPN general purpose transistor

Product data sheet
Supersedes data of 2000 Jul 28

2004 Jan 16

NPN general purpose transistor

BCX19

FEATURES

- High current (500 mA)
- Low voltage (45 V).

APPLICATIONS

- General purpose amplification
- Saturated switching and driver applications.

DESCRIPTION

NPN transistor in a SOT23 plastic package.
PNP complement: BCX17.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BCX19	U1*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

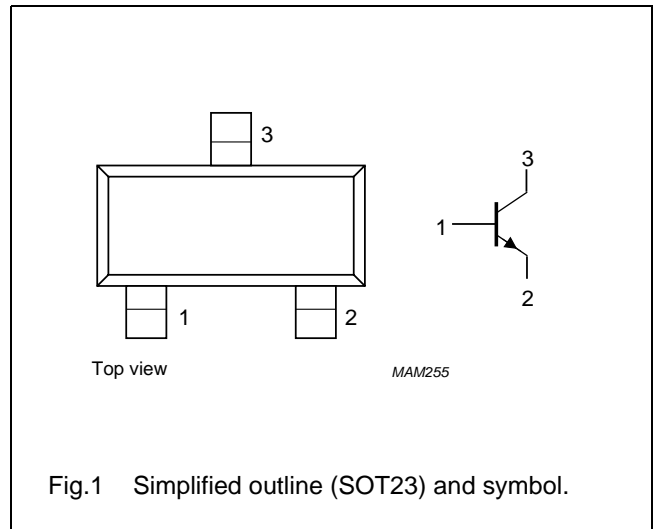


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BCX19	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	50	V
V _{CEO}	collector-emitter voltage	open base; I _C = 10 mA	–	45	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	500	mA
I _{CM}	peak collector current		–	1	A
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 150\text{ °C}$	–	–	5	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V};$ note 1				
		$I_C = 100\text{ mA}$	100	–	600	
		$I_C = 300\text{ mA}$	70	–	–	
		$I_C = 500\text{ mA}$	40	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ note 2	–	–	620	mV
V_{BE}	base-emitter voltage	$I_C = 500\text{ mA}; V_{CE} = 1\text{ V};$ notes 1 and 2	–	–	1.2	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	5	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz

Notes

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.
2. V_{BE} decreases by approximately -2 mV/°C with increasing temperature.

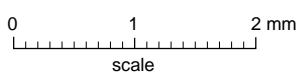
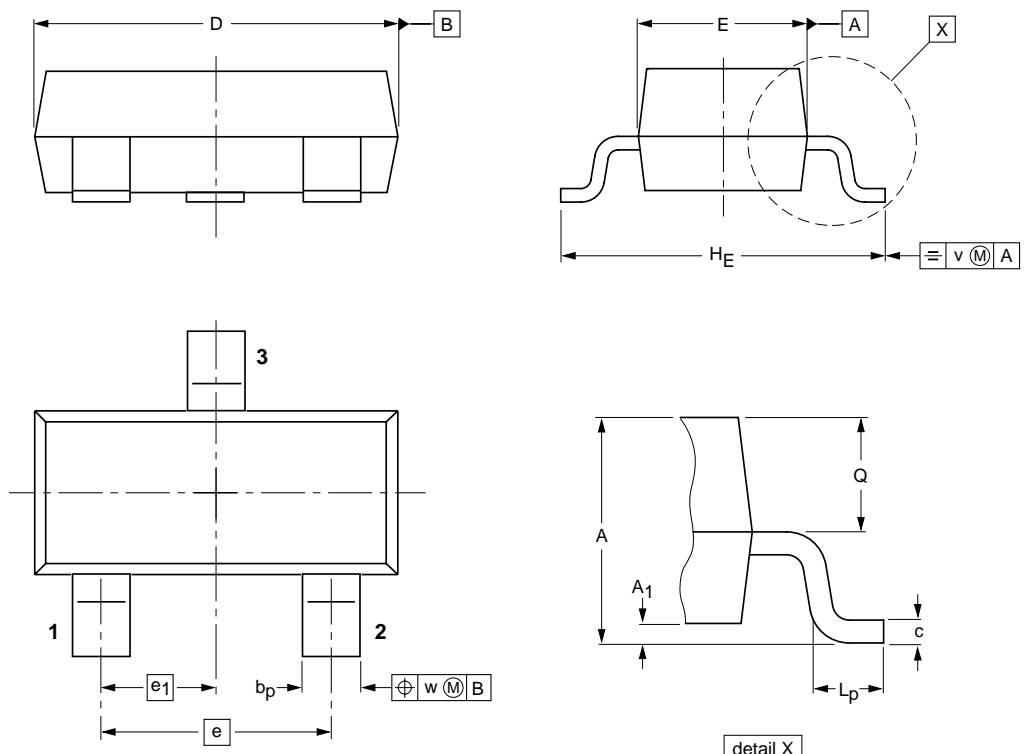
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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16